Quantum Dot Lasers Grown on Silicon

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Silicon Photonics

Increasing demand for bandwidth





Silicon offers an economic-friendly solution

The Flaws of Using Silicon





 Dislocations from the GaAs-Si mismatch cause diminishing device performance

Quantum Dot Laser Structure





Molecular Beam Epitaxy



Quantum Dots

Quantum well

- 2-D confinement
- Discrete energy levels







Quantum Dot

- 3-D confinement
- Discrete energy levels



Characterizing a Laser

Modular Integrating Sphere



Gathers power output from laser



Optical Spectrum Analyzer (OSA)



Gathers wavelengths emitted from laser



Power vs. Wavelength

Power vs. Current

Device Threshold



GaAs (red) Avg: 44.2 mA

Quantum Dot (blue) Avg: 42.1 mA

• Thresholds for quantum dot lasers are comparable to those grown on GaAs

Device Injection Efficiency



Efficiency of quantum dot lasers comparable to GaAs

Efficiency

Device width (um)

Summary

- GaP/Si devices performed within range of similar GaAs devices
- Commercial viability
- Applications in data centers

Future steps

Comparing different compositions and thicknesses of cladding layers



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